

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	125	V
Collector-Emitter Voltage	V <sub>CEO</sub>	125	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	1	A
Peak Pulse Current (Note 5)	I <sub>CM</sub>	3	A
Base Current	I <sub>B</sub>	500	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

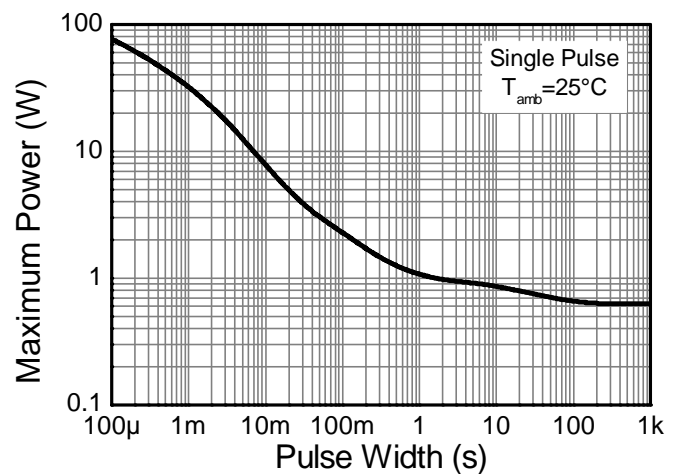
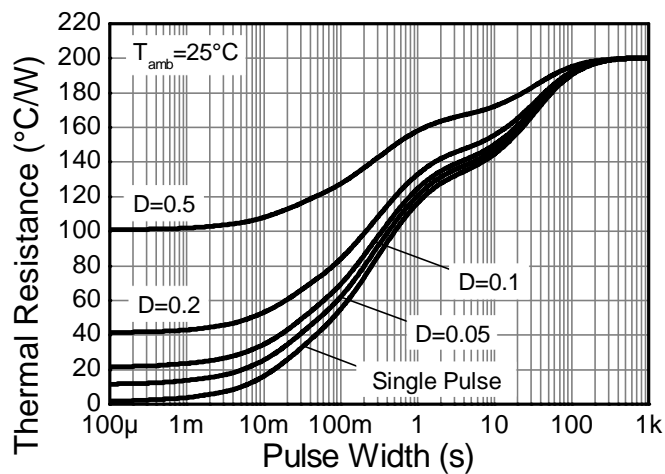
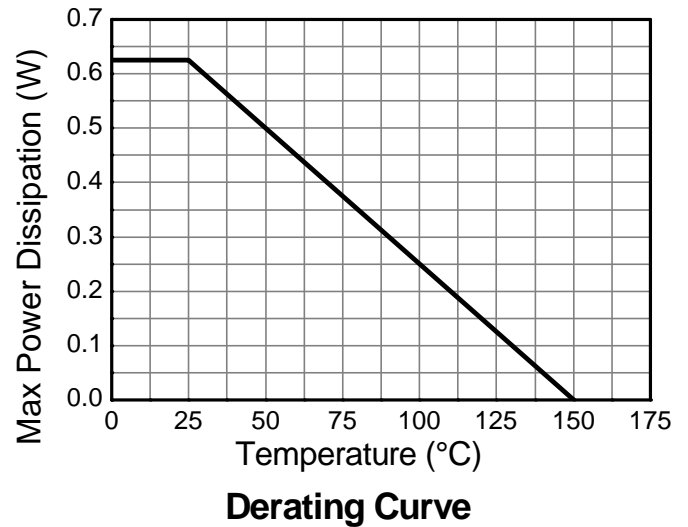
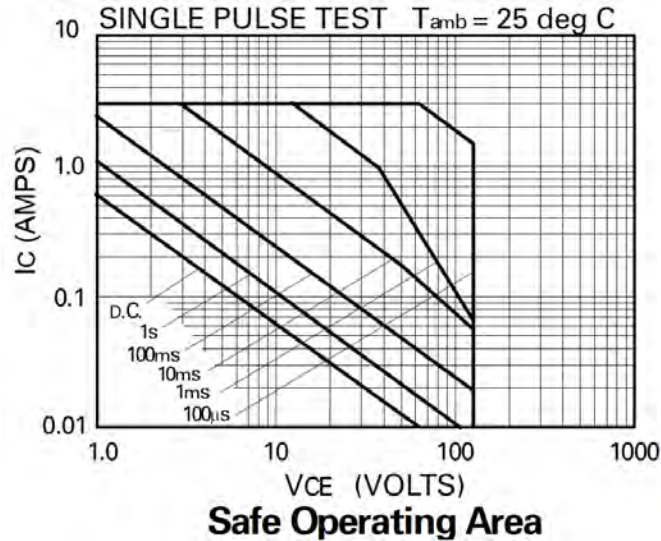
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	625	mW
Power Dissipation (Note 6)	P <sub>D</sub>	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R <sub>θJL</sub>	194	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
5. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  6. Same as note 5, except the device is measured at t ≤ 5 sec.
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

## Thermal Characteristics and Derating information

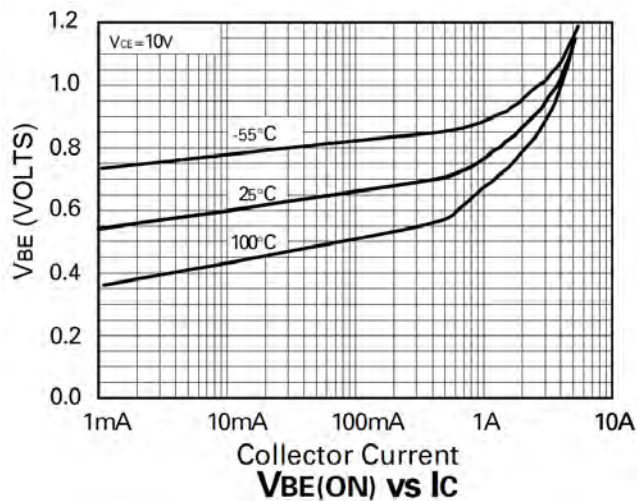
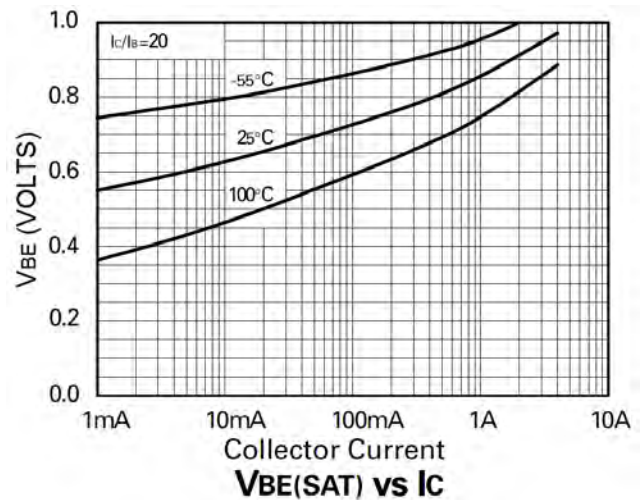
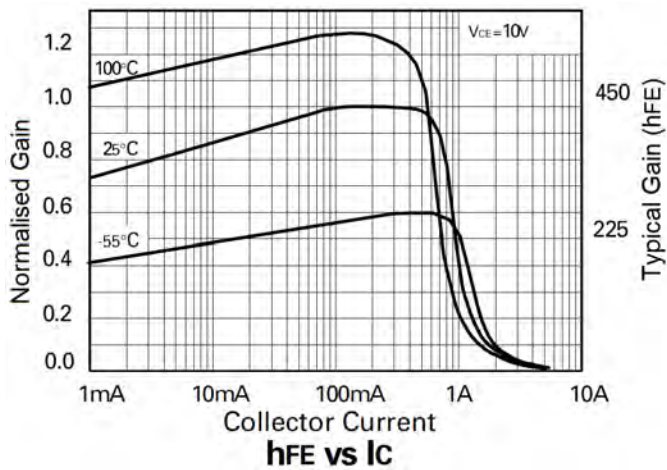
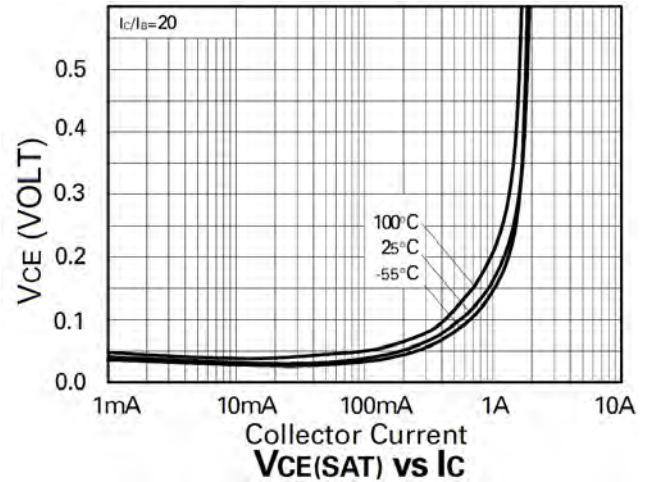
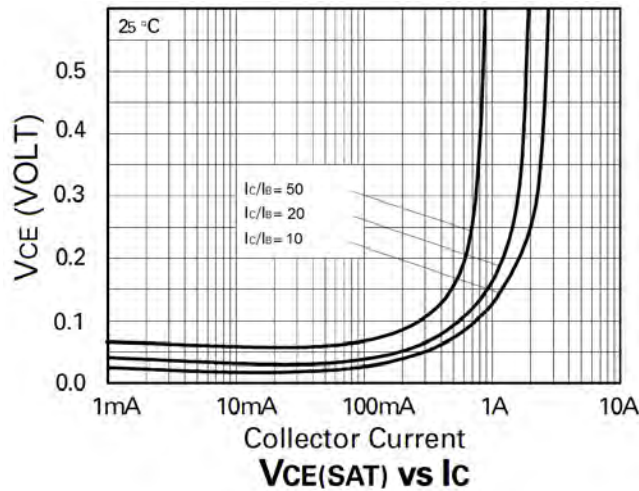


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	125	250	-	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	125	160	-	V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3	-	V	I <sub>E</sub> = 100μA
Collector Cut-off Current	I <sub>CBO</sub>	-	<10	100	nA	V <sub>CB</sub> = 100V
Emitter Cut-off Current	I <sub>EBO</sub>	-	<10	100	nA	V <sub>EB</sub> = 6.0V
Collector Emitter Cut-off Current	I <sub>CES</sub>	-	<10	100	nA	V <sub>CES</sub> = 100V
Static Forward Current Transfer Ratio (Note 9)	h <sub>FE</sub>	200 300 100 -	400 450 140 18	- - - -	-	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V I <sub>C</sub> = 200mA, V <sub>CE</sub> = 10V I <sub>C</sub> = 1A, V <sub>CE</sub> = 10V I <sub>C</sub> = 3A, V <sub>CE</sub> = 10V
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	- - - -	26 70 160 165	50 150 220 250	mV	I <sub>C</sub> = 0.1A, I <sub>B</sub> = 10mA I <sub>C</sub> = 0.5A, I <sub>B</sub> = 50mA I <sub>C</sub> = 0.5A, I <sub>B</sub> = 10mA I <sub>C</sub> = 1A, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	0.85	1.0	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(on)</sub>	-	0.70	1.0	V	I <sub>C</sub> = 1A, V <sub>CE</sub> = 10V
Transition Frequency	f <sub>T</sub>	100	155	-	MHz	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 10V, f = 100MHz
Collector Output Capacitance	C <sub>obo</sub>	-	7	15	pF	V <sub>CB</sub> = 10V, f = 1MHz
Turn-On Time	t <sub>(on)</sub>	-	60	-	ns	V <sub>CC</sub> = 50V, I <sub>C</sub> = 0.5A,
Turn-Off Time	t <sub>(off)</sub>	-	1300	-	ns	I <sub>B1</sub> = -I <sub>B2</sub> = 50mA

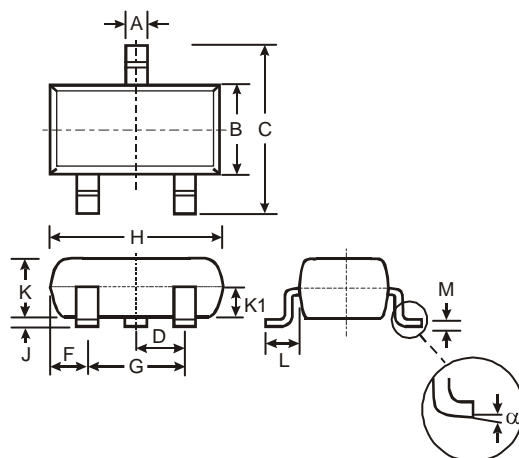
Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



## Package Outline Dimensions

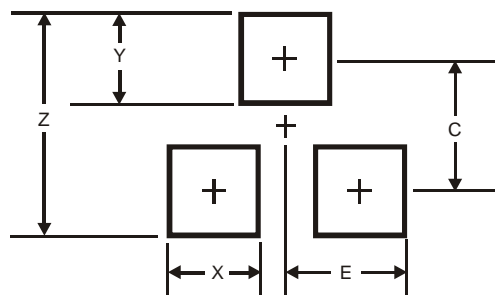
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
$\alpha$	0°	8°	-
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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